



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126C Plastic-Encapsulate Transistors

2SD886 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

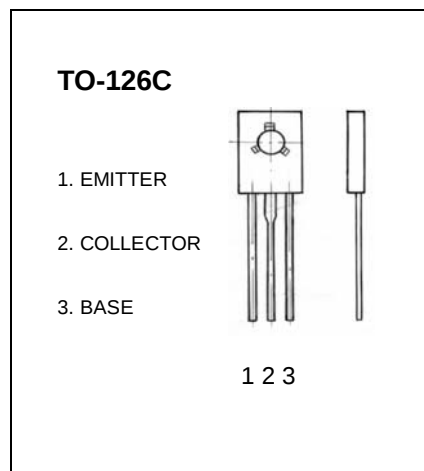
I_{CM} : 3 A

Collector-base voltage

$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=5mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3V, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=20mA$	100			
	$h_{FE(2)}$	$V_{CE}=2V, I_C=1A$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2A, I_B=200mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2A, I_B=200mA$			2	V
Transition frequency	f_T	$V_{CE}=5V, I_C=100mA$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		45		pF